

Abstract of the Disclosure

A semiconductor laser device having a smooth cleavage plane is provided. The provided laser device includes a current injection ridge and force distribution ridges formed adjacent to the current injection ridge, which protrudes from an upper surface of a mesa structure. The mesa structure is formed of multi-semiconductor material layers including a laser resonance layer and cladding layers disposed above and below the resonance layer. The current injection ridge and the force distribution ridges distribute a scribing force when cleaving the laser device so that the smooth cleavage planes are obtained. Defects are prevented in the current injection ridge due to the distribution of force when bonding flip chips.